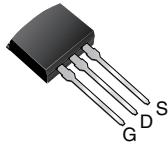
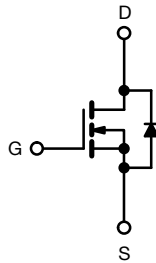
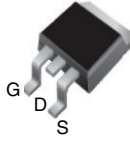


## Power MOSFET

 I<sup>2</sup>PAK (TO-262)

 D<sup>2</sup>PAK (TO-2)


N-Channel MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	500
R <sub>DS(on)</sub> max. (Ω)	V <sub>GS</sub> = 10 V 1.40
Q <sub>g</sub> max. (nC)	24
Q <sub>gs</sub> (nC)	6.3
Q <sub>gd</sub> (nC)	11
Configuration	Single

### FEATURES

- Low gate charge Q<sub>g</sub> results in simple drive requirement
- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Effective C<sub>oss</sub> specified
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



RoHS\*  
Available  
HALOGEN  
FREE  
Available

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching

### TYPICAL SMPS TOPOLOGIES

- Two transistor forward
- Half bridge and full bridge

ORDERING INFORMATION			
Package	D <sup>2</sup> PAK (TO-263)	D <sup>2</sup> PAK (TO-263)	I <sup>2</sup> PAK (TO-262)
Lead (Pb)-free and Halogen-free	SiHF830AS-GE3	SiHF830ASTRL-GE3 <sup>a</sup>	SiHF830AL-GE3 <sup>a</sup>
Lead (Pb)-free	IRF830ASPbF	IRF830ASTRLPbF <sup>a</sup>	IRF830ALPbF

### Note

a. See device orientation

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	500	V
Gate-Source Voltage	V <sub>GS</sub>	± 30	
Continuous Drain Current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	A
		T <sub>C</sub> = 100 °C	
Pulsed Drain Current <sup>a, e</sup>	I <sub>DM</sub>	20	
Linear Derating Factor		0.59	W/°C
Single Pulse Avalanche Energy <sup>b, e</sup>	E <sub>AS</sub>	230	mJ
Avalanche Current	I <sub>AR</sub>	5.0	A
Repetitive Avalanche Energy <sup>a</sup>	E <sub>AR</sub>	7.4	mJ
Maximum Power Dissipation	P <sub>D</sub>	T <sub>A</sub> = 25 °C	W
		T <sub>C</sub> = 25 °C	
Peak Diode Recovery dV/dt <sub>c</sub> <sup>e</sup>	dV/dt	5.3	V/ns
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering Recommendations (Peak temperature) <sup>d</sup>	for 10 s	300	

### Notes


- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- Starting T<sub>J</sub> = 25 °C, L = 18 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 5.0 A (see fig. 12)
- I<sub>SD</sub> ≤ 5.0 A, di/dt ≤ 370 A/μs, V<sub>DD</sub> ≤ V<sub>DS</sub>, T<sub>J</sub> ≤ 150 °C
- 1.6 mm from case
- Uses SiHF830A data and test conditions



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB mounted, steady-state) <sup>a</sup>	R <sub>thJA</sub>	-	40	°C/W
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	-	1.7	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material)

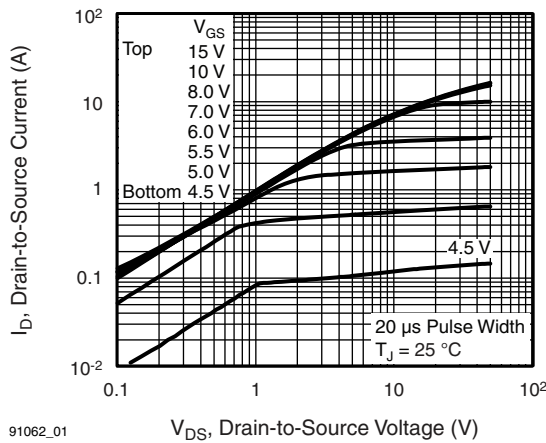
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA	500	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA <sup>d</sup>	-	0.60	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	-	4.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 30 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V	-	-	25	μA
		V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	250	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.0 A <sup>b</sup>	-	-	1.4	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 3.0 A <sup>d</sup>	2.8	-	-	S
<b>Dynamic</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5 <sup>d</sup>	-	620	-	pF
Output Capacitance	C <sub>oss</sub>		-	93	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	4.3	-	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 1.0 V, f = 1.0 MHz	-	886	-
			V <sub>DS</sub> = 400 V, f = 1.0 MHz	-	27	-
Effective Output Capacitance	C <sub>oss eff.</sub>	V <sub>DS</sub> = 0 V to 400 V <sup>c, d</sup>	-	39	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.0 A, V <sub>DS</sub> = 400 V, see fig. 6 and 13 <sup>b, d</sup>	-	-	24	nC
Gate-Source Charge	Q <sub>gs</sub>		-	-	6.3	
Gate-Drain Charge	Q <sub>gd</sub>		-	-	11	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 250 V, I <sub>D</sub> = 5.0 A, R <sub>g</sub> = 14 Ω, R <sub>D</sub> = 49 Ω, see fig. 10 <sup>b, d</sup>	-	10	-	ns
Rise Time	t <sub>r</sub>		-	21	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	21	-	
Fall Time	t <sub>f</sub>		-	15	-	
Gate Input Resistance	R <sub>g</sub>	f = 1 MHz, open drain	1.7	-	10.7	Ω
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	5.0	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>		-	-	20	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 5.0 A, V <sub>GS</sub> = 0 V <sup>b</sup>	-	-	1.5	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 5.0 A, dI/dt = 100 A/μs <sup>b, d</sup>	-	430	650	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	2.0	3.0	
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )				

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %
- c. C<sub>oss eff.</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80 % V<sub>DS</sub>
- d. Uses SiHF830A data and test conditions

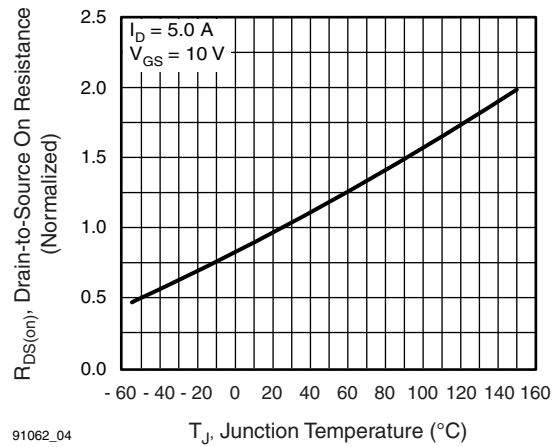


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



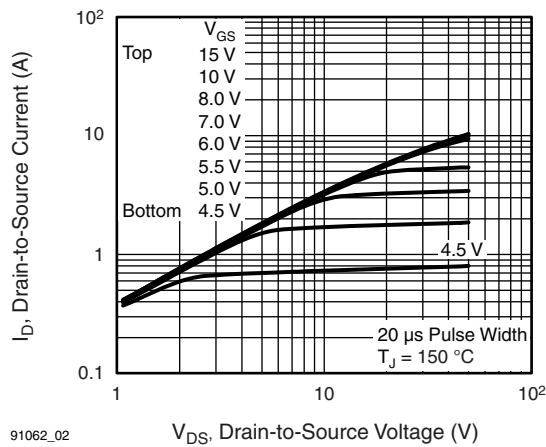
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**Fig. 1 - Typical Output Characteristics**



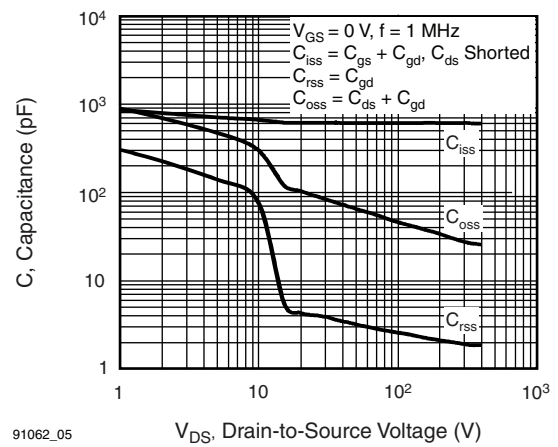
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**Fig. 4 - Normalized On-Resistance vs. Temperature**



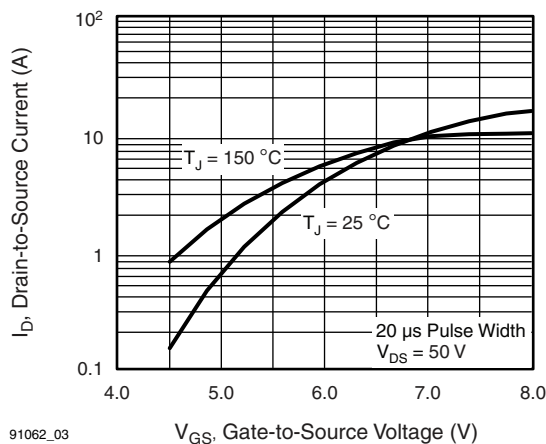
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**Fig. 2 - Typical Output Characteristics**



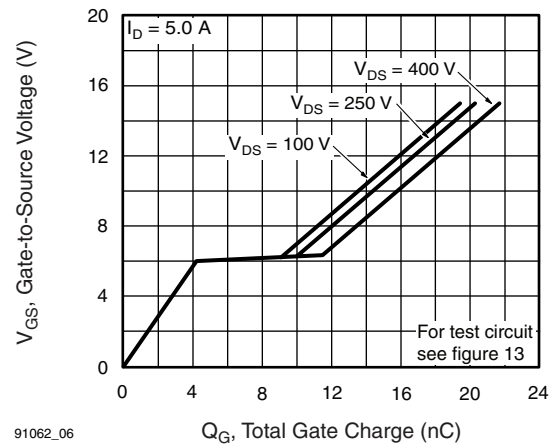
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**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



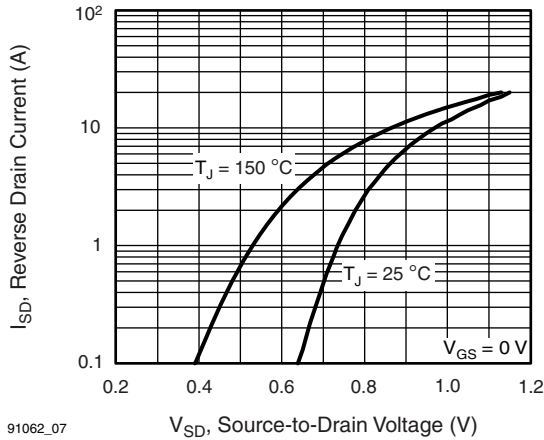
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**Fig. 3 - Typical Transfer Characteristics**



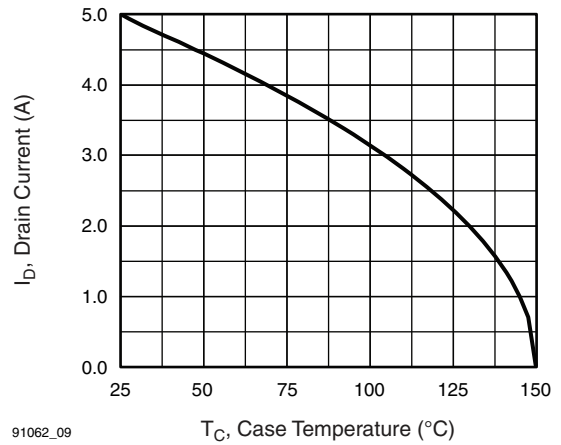
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**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



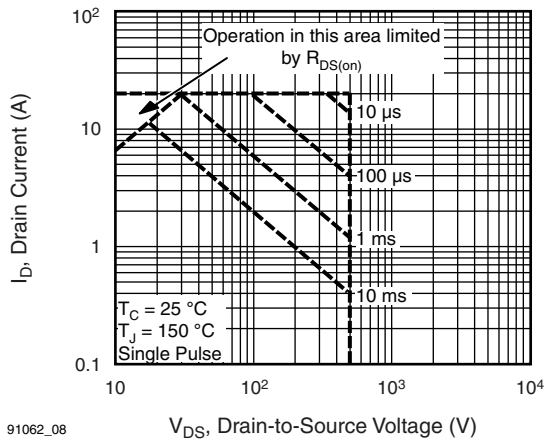
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



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Fig. 9 - Maximum Drain Current vs. Case Temperature



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Fig. 8 - Maximum Safe Operating Area

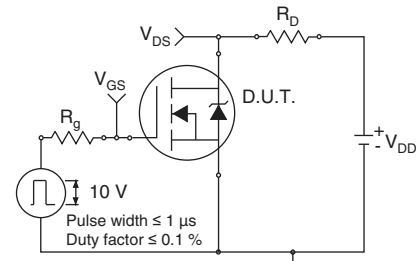


Fig. 10a - Switching Time Test Circuit

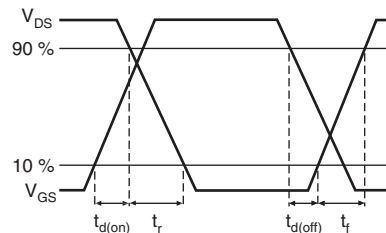
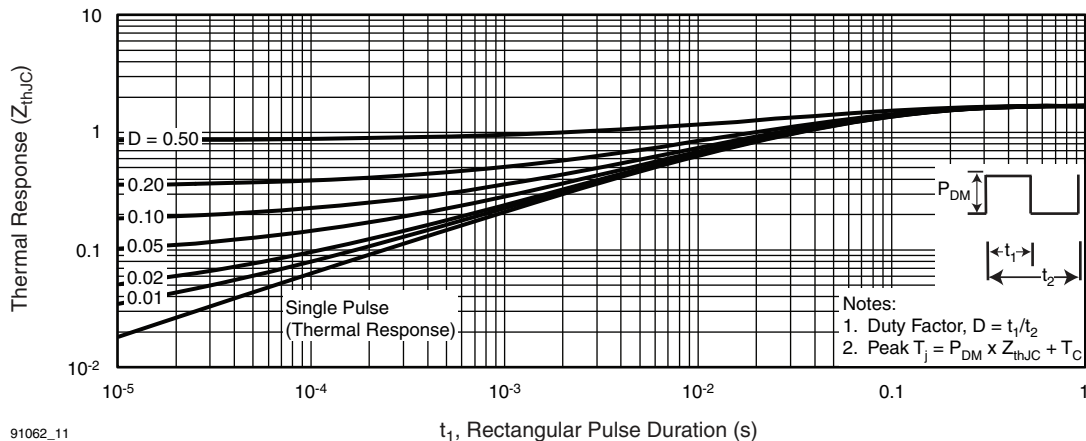


Fig. 10b - Switching Time Waveforms



91062\_11

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

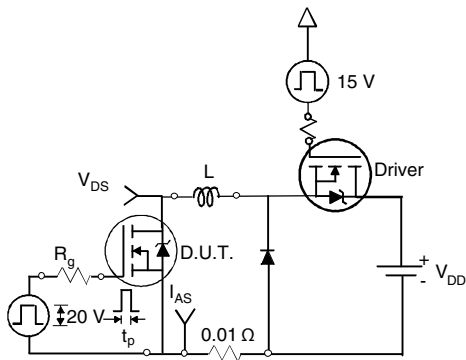


Fig. 12a - Unclamped Inductive Test Circuit

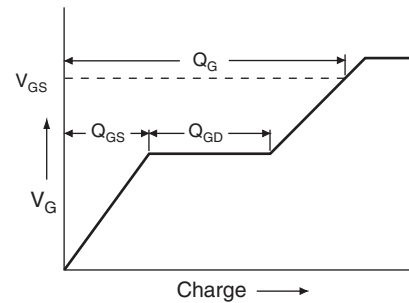


Fig. 13a - Maximum Avalanche Energy vs. Drain Current

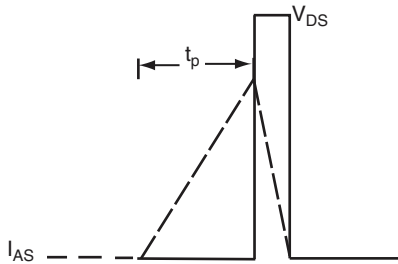


Fig. 12b - Unclamped Inductive Waveforms

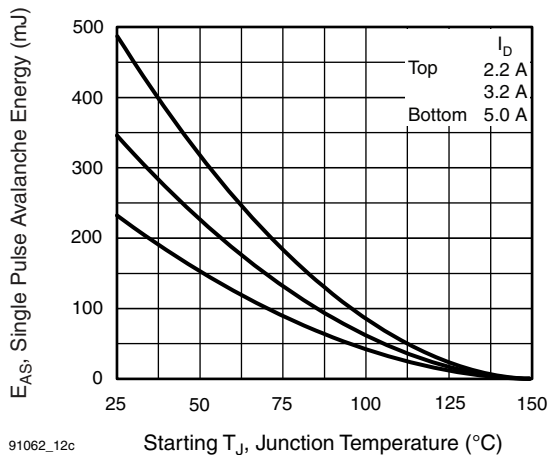


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

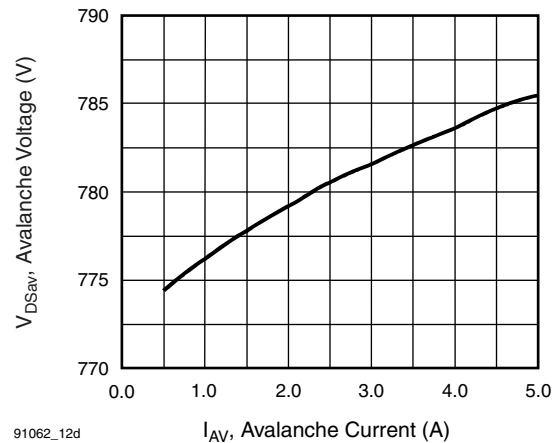


Fig. 12d - Basic Gate Charge Waveform

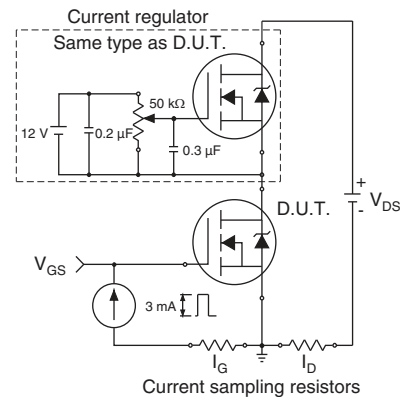
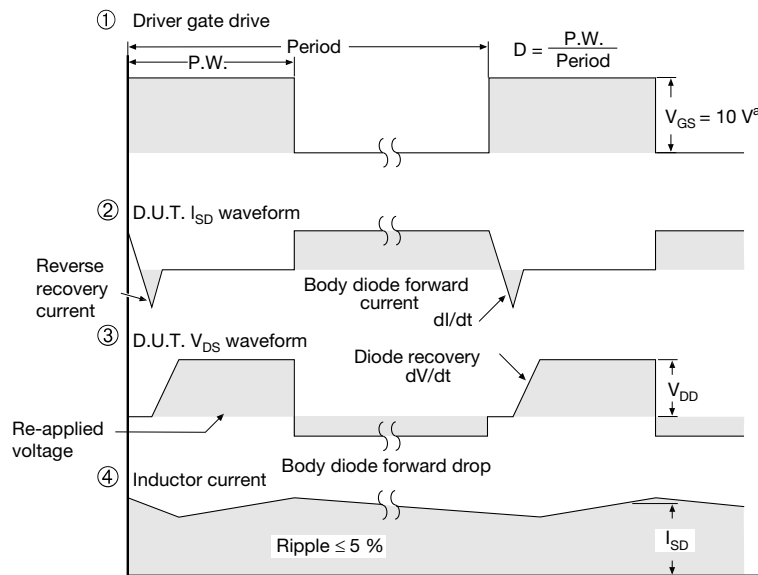
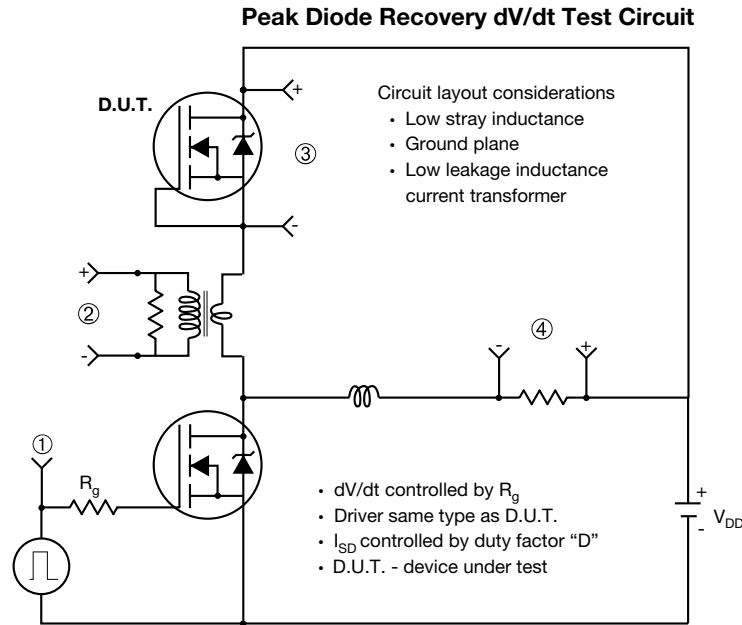


Fig. 13b - Gate Charge Test Circuit



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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### TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

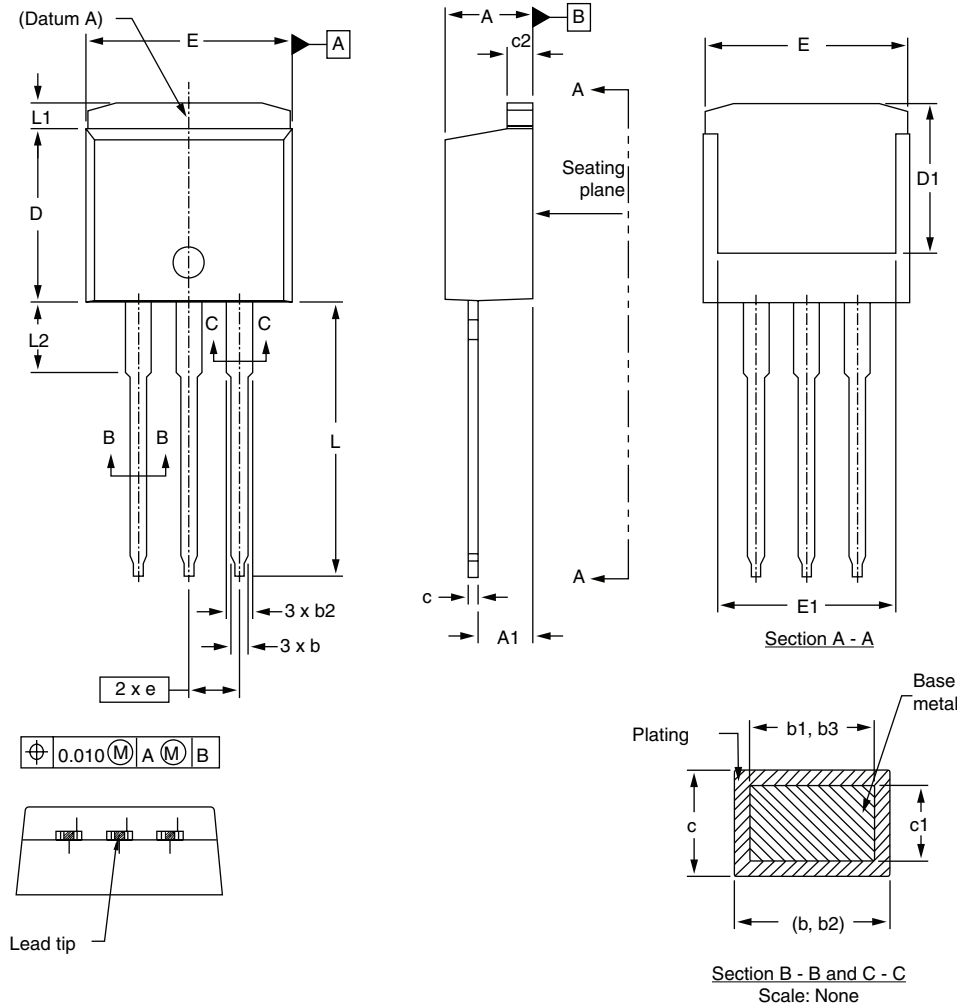
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08  
DWG: 5970

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

## I<sup>2</sup>PAK (TO-262) (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	2.03	3.02	0.080	0.119
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D	8.38	9.65	0.330	0.380
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
L	13.46	14.10	0.530	0.555
L1	-	1.65	-	0.065
L2	3.56	3.71	0.140	0.146

ECN: S-82442-Rev. A, 27-Oct-08  
DWG: 5977

### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
3. Thermal pad contour optional within dimension E, L1, D1, and E1.
4. Dimension b1 and c1 apply to base metal only.



**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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